

PNZ123S

Silicon NPN Phototransistor

For optical control systems

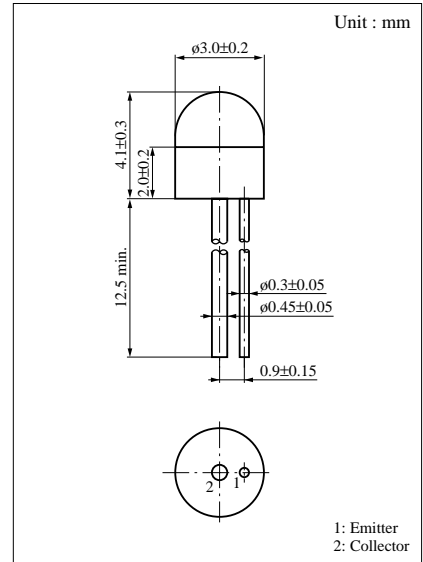
Can be combined with LN62S to form an photo interrupter

■ Features

- High sensitivity
- Low dark current
- Fast response : $t_r = 3.5 \mu s$ (typ.)
- Small size ($\phi 3$) ceramic package

■ Absolute Maximum Ratings (Ta = 25°C)

Parameter	Symbol	Ratings	Unit
Collector to emitter voltage	V_{CEO}	20	V
Emitter to collector voltage	V_{ECO}	5	V
Collector current	I_C	10	mA
Collector power dissipation	P_C	50	mW
Operating ambient temperature	T_{opr}	-25 to +85	°C
Storage temperature	T_{stg}	-30 to +100	°C

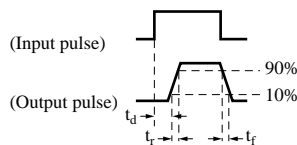
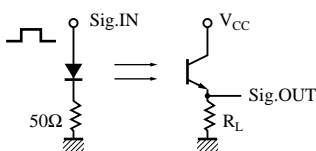


■ Electro-Optical Characteristics (Ta = 25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Dark current	I_{CEO}	$V_{CE} = 10V$		1	100	nA
Collector photo current	$I_{CE(L)}$	$V_{CE} = 10V, L = 1000 lx^{*1}$	400		700	μA
Peak sensitivity wavelength	λ_p	$V_{CE} = 10V$		800		nm
Acceptance half angle	θ	Measured from the optical axis to the half power point		30		deg.
Rise time	t_r^{*2}	$V_{CC} = 10V, I_{CE(L)} = 1mA, R_L = 100\Omega$		3.5		μs
Fall time	t_f^{*2}			5		μs

*1 Measurements were made using a tungsten lamp (color temperature T = 2856K) as a light source.

*2 Switching time measurement circuit



t_d : Delay time

t_r : Rise time (Time required for the collector photo current to increase from 10% to 90% of its final value)

t_f : Fall time (Time required for the collector photo current to decrease from 90% to 10% of its initial value)

